CQ3400A

30V N-Channel MOSFET

General Description

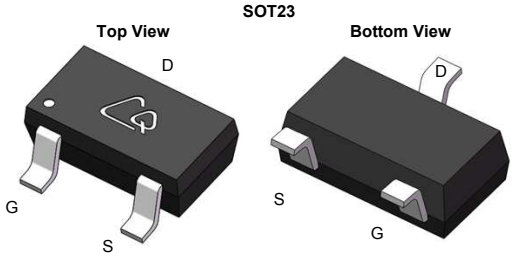
The CQ3400A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

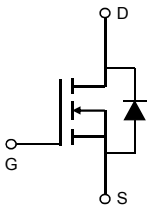
Product Summary

V_{DS}	30V
I_D (at V_{GS}=10V)	5.7A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 26.5mΩ
$R_{DS(ON)}$ (at V_{GS} = 4.5V)	< 32mΩ
$R_{DS(ON)}$ (at V_{GS} = 2.5V)	< 48mΩ

Green Product

SOT23





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current	T_A=25°C	I_D	5.7	A
	T_A=70°C		4.7	
Pulsed Drain Current [C]		I_{DM}	30	
Power Dissipation [B]	T_A=25°C	P_D	1.4	W
	T_A=70°C		0.9	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	70	90	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		100	125	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	63	80	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	μA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±12V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	0.65	1.05	1.45	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=5.7A		18	26.5	mΩ
		T_J=125°C		28	38	
		V_{GS}=4.5V, I_D=5A		19	32	mΩ
		V_{GS}=2.5V, I_D=3A		24	48	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=5.7A		33		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		630		pF
C_{oss}	Output Capacitance			75		pF
C_{rss}	Reverse Transfer Capacitance			50		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	1.5	3	4.5	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=5.7A		6	7	nC
Q_{gs}	Gate Source Charge			1.3		nC
Q_{gd}	Gate Drain Charge			1.8		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=2.6Ω, R_{GEN}=3Ω		3		ns
t_r	Turn-On Rise Time			2.5		ns
$t_{D(off)}$	Turn-Off DelayTime			25		ns
t_f	Turn-Off Fall Time			4		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=5.7A, dI/dt=100A/μs		8.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=5.7A, dI/dt=100A/μs		2.6		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

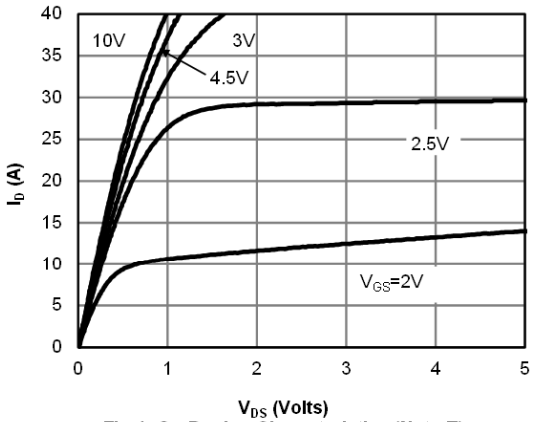


Fig 1: On-Region Characteristics (Note E)

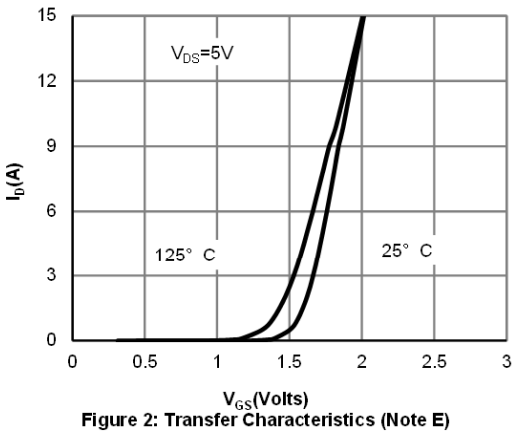


Figure 2: Transfer Characteristics (Note E)

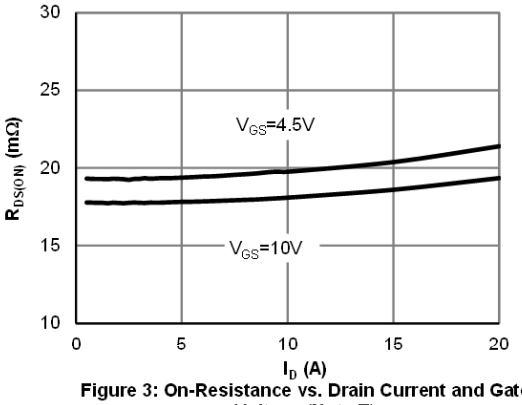


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

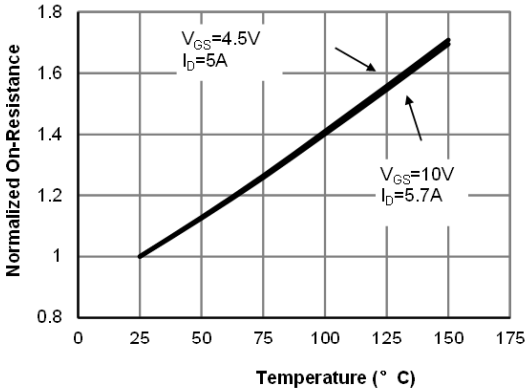


Figure 4: On-Resistance vs. Junction Temperature (Note E)

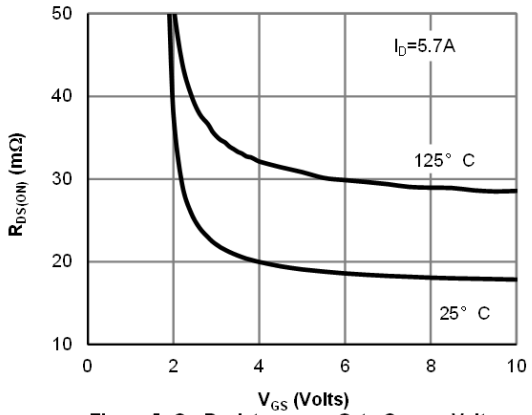


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

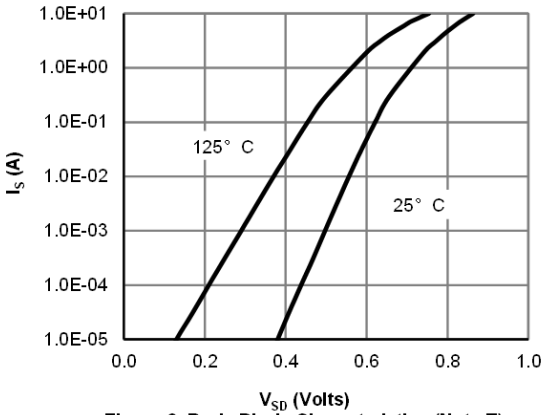


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

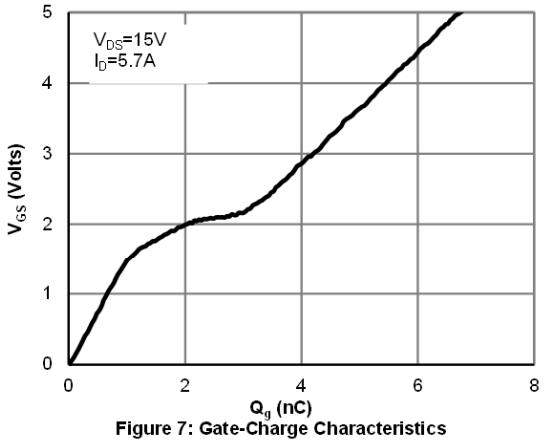


Figure 7: Gate-Charge Characteristics

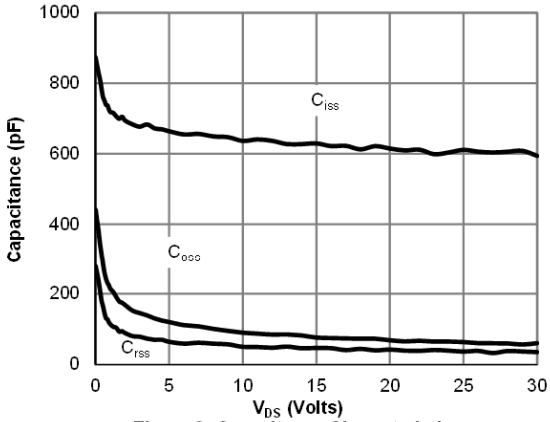


Figure 8: Capacitance Characteristics

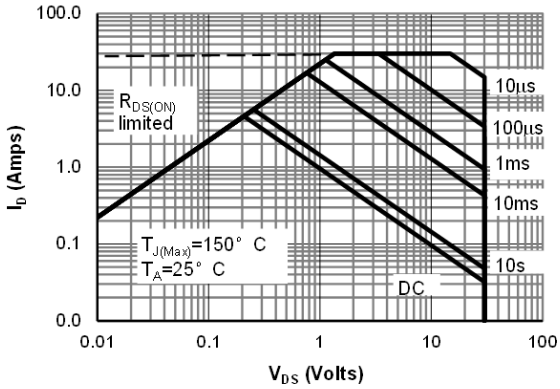


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

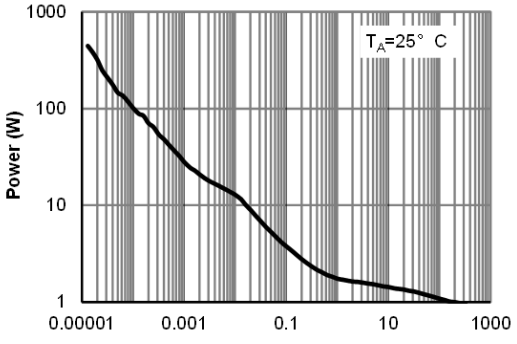


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

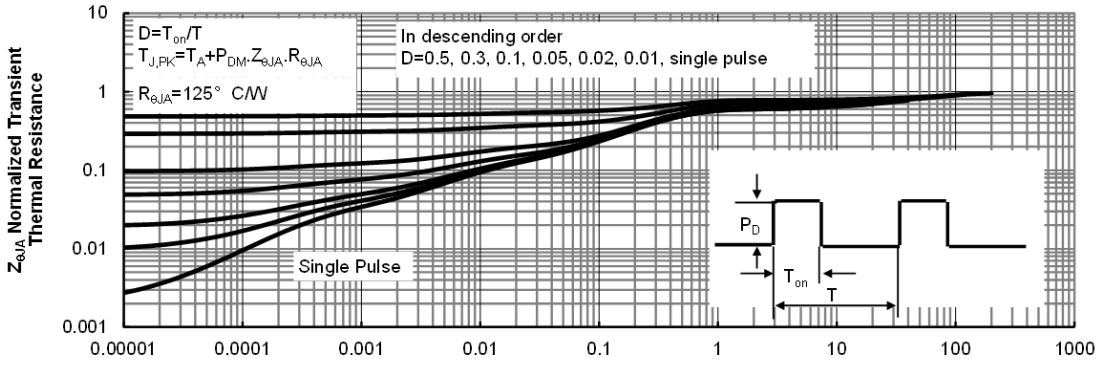
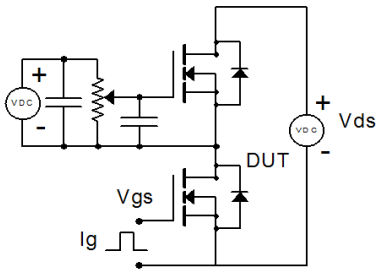
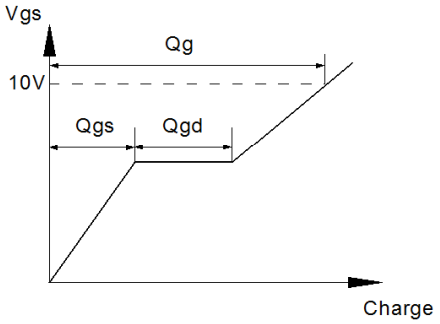


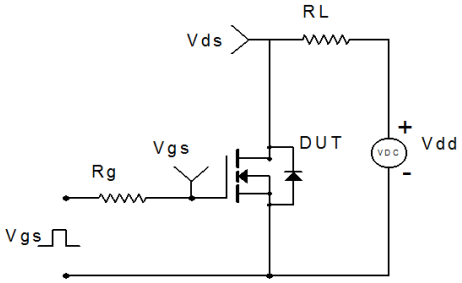
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

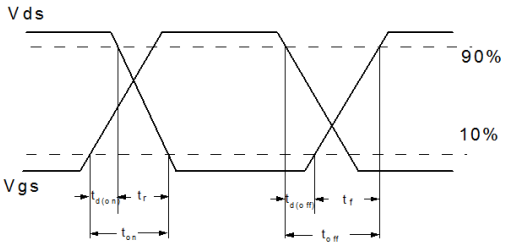
Gate Charge Test Circuit & Waveform



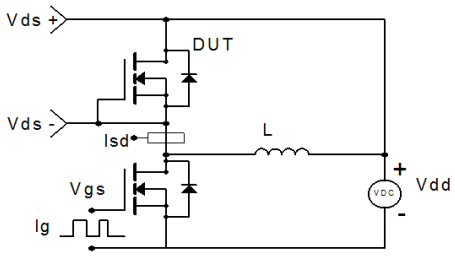


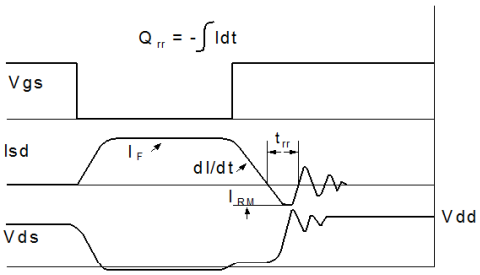
Resistive Switching Test Circuit & Waveforms





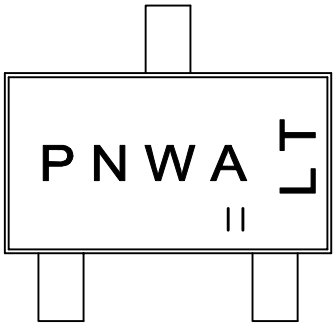
Diode Recovery Test Circuit & Waveforms





Document No.	PDCQ-00005
Version	A
Title	CQ3400A Marking Description

SOT-23 PACKAGE MARKING DESCRIPTION



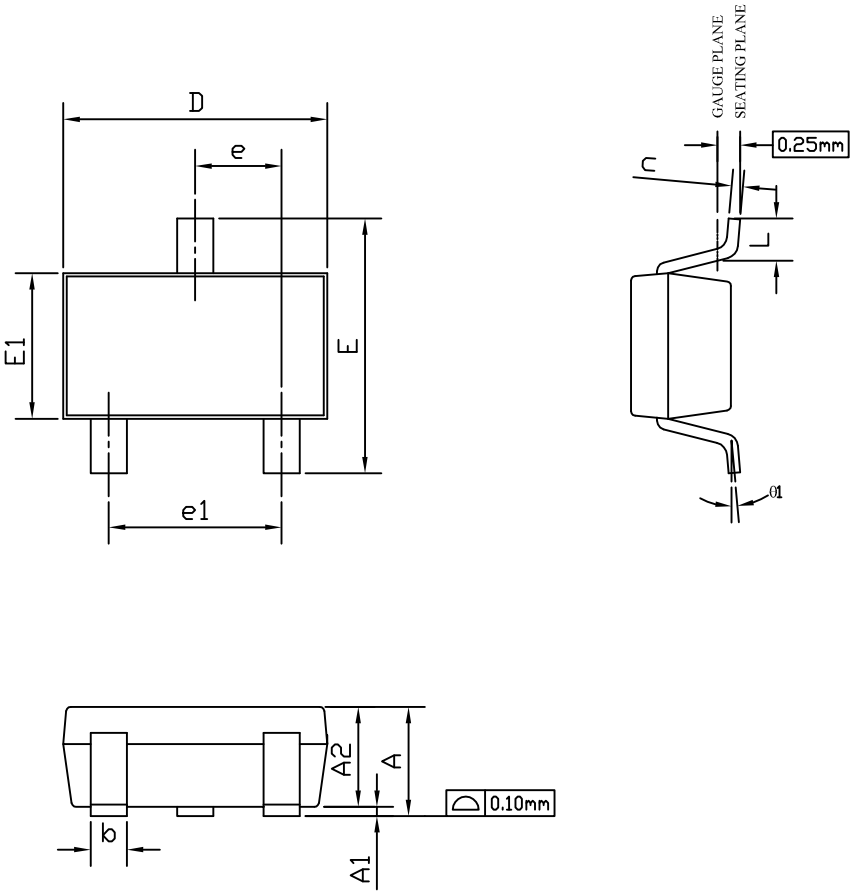
Green product

NOTE:
P - Package and product type
N - Last digital of product number
W - Week code
A - Assembly location code
L&T - Assembly lot code

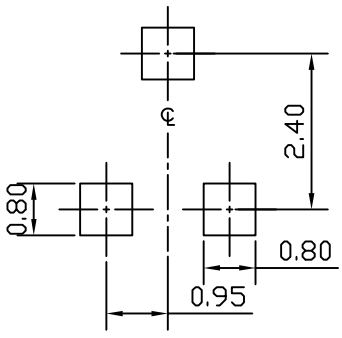
PART NO.	DESCRIPTION	CODE (PN)
CQ3400A	Green product	X0

Document No.	POCQ-00005
Version	A

SOT23 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UNIT: mm

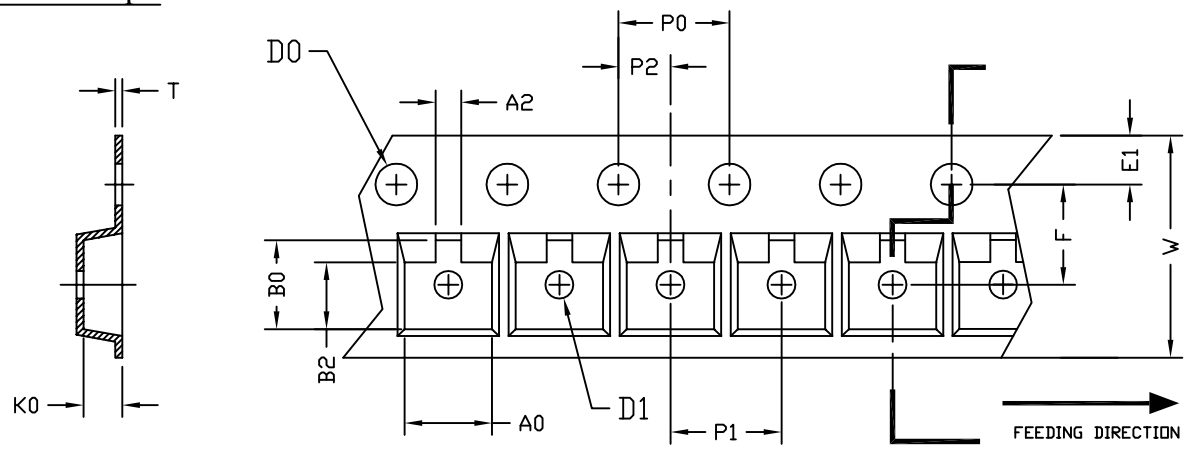
SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	——	1.25	0.033	——	0.049
A1	0.00	——	0.13	0.000	——	0.005
A2	0.70	1.00	1.15	0.028	0.039	0.045
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.08	0.13	0.20	0.003	0.005	0.008
D	2.80	2.90	3.10	0.110	0.114	0.122
E	2.60	2.80	3.00	0.102	0.110	0.118
E1	1.40	1.60	1.80	0.055	0.063	0.071
e	0.95 BSC			0.037 BSC		
e1	1.90 BSC			0.075 BSC		
L	0.30	——	0.60	0.012	——	0.024
θ1	0°	5°	8°	0°	5°	8°

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH OR GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 5 MILS EACH.
2. TOLERANCE ±0.100 mm (4 mil) UNLESS OTHERWISE SPECIFIED.
3. DIMENSION L IS MEASURED IN GAUGE PLANE.
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS
   ARE NOT NECESSARILY EXACT.
5. ALL DIMENSIONS ARE IN MILLIMETERS.

SOT23 Tape and Reel Data

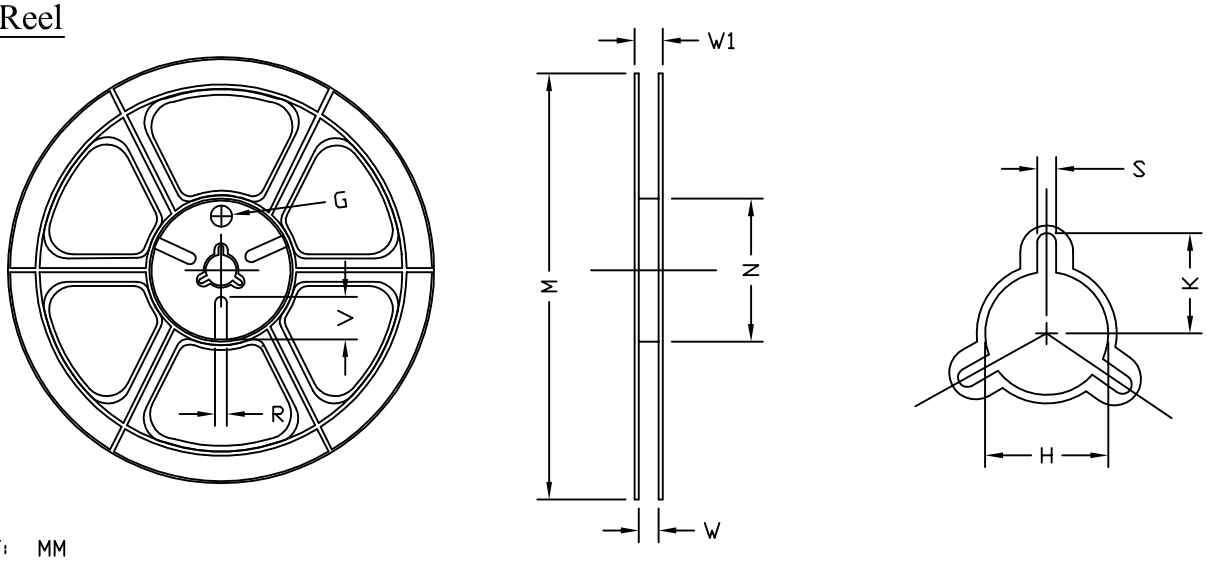
SOT23 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	W	E1	F	P0	P1	P2	T	A2	B2
SOT23 (8 mm)	3.05-3.40	3.00-3.38	1.20- 1.47	1.55 ±0.05	1.00 ±0.25	8.00 ±0.30	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.18 -0.25	0.84-1.24	2.29-2.69

SOT23 Reel



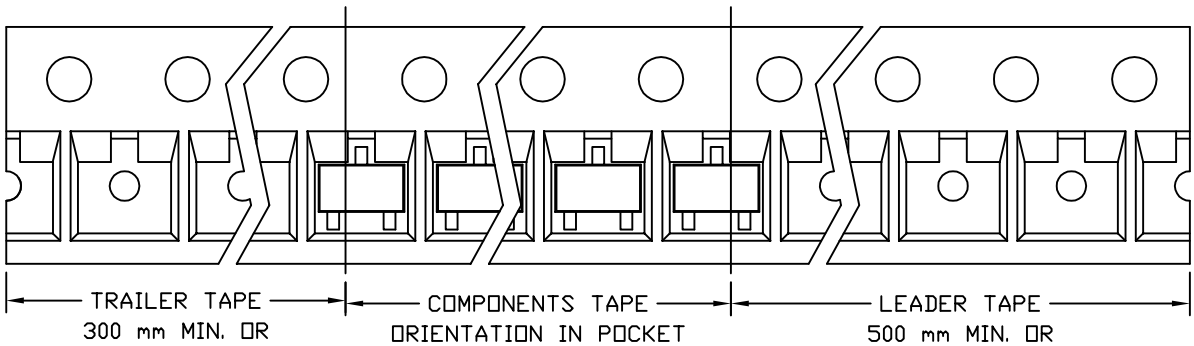
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8 mm	ø178	ø178.00 ±1.00	ø54.00 ±0.50	9.00 ±0.30	11.40 ±1.00	ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	ø9.00	5.00	18.00

SOT23 Tape

Leader / Trailer & Orientation

Unit Per Reel: 3000pcs



CQAOS Semiconductor
Product Reliability Report

CQ3400A, rev A

Plastic Encapsulated Device

Chongqing Alpha & Omega Semiconductor, Limited

Apr, 2020

This CQAOS product reliability report summarizes the qualification result for CQ3400A. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that CQ3400A passes CQAOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow@260°C (MSL 1)	-	4620 pcs	0	JESD22-A113
HAST	130°C , 85%RH, 33.3 psia, Vds = 80% of Vdsmax	96 hours	693 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vds = 80% of Vdsmax	1000 hours	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	1000 cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 150°C	1000 hours	693 pcs	0	JESD22-A103
IOL	∆ Tj = 100°C	15000 cycles	693 pcs	0	MIL-STD-750 Method 1037

Note: The reliability data presents total of available generic data up to the published date.
Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

II. Reliability Evaluation

FIT rate (per billion): 1.91
MTTF = 59839 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9$ **/ [**2 (N) (H) (Af)**] =** 1.91
MTTF = 10^9 / FIT = 59839 years
Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval
N = Total Number of units from burn-in tests
H = Duration of burn-in testing
Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)
Acceleration Factor [**Af**] = **Exp** [Ea / **k** (1/Tj u – 1/Tj s)]
Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16
Tj u =The use junction temperature in degree (Kelvin), K = C+273.16
k = Boltzmann's constant, 8.617164 X 10^{-5}eV / K